









B1D10065KS

650V ▲ 10A ▲ SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type

Excellent surge capability
Easy paralleling due to positive V_F temperature coefficient

Temperature independent switching

Low forward voltage

TO-220 ISO-2L ceramic package ▲ 2.5kV isolation voltage

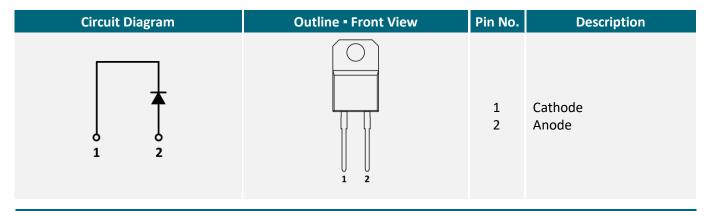
SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)		Characteristics
Operating Temperature Range	T _J	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V_{RRM}	650V
Continuous Forward Current at T _C = 145°C	I _F	10A
Total Capacitive Charge (T _J = 25°C)	\mathbf{Q}_{c}	29nC
Capacitance Stored Energy (V _R = 400V)	E _C	7.5µJ
Diode Forward Voltage (T _J = 175°C, I _F = 10A)	V _F	1.75V
Power Dissipation	P _{TOT}	89W

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
∳ // e			PFC	*		

PIN DESCRIPTION



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ABSOLUT MAXIMUM RATINGS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V_{RSM}	650	V
Continuous Forward Current	T _C = 25°C	I _F	28	Α
Continuous Forward Current	T _C = 145°C	I _F	10	Α
Non-Repetitive Forward Surge Current	T_C = 25°C, t_p = 10ms, Half Sine Wave	I _{FSM}	75	Α
I ² t Value	$T_C = 25^{\circ}C$, $t_p = 10$ ms	∫i²dt	28.12	A^2s
Power Dissipation	T _C = 25°C	P _{TOT}	89	W
Power Dissipation	T _C = 110°C	P_{TOT}	38	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +175	°C
Isolation Voltage	AC, t = 1s	V_{ISOL}	2500	V_{RMS}
TO-220 Mounting Torque	M3 Screw		0.7	Nm

ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	650			V
Diode Forward Voltage	$I_F = 10A, T_J = 25^{\circ}C$	V_{F}		1.43		V
Diode Forward Voltage	$I_F = 10A, T_J = 175^{\circ}C$	V_{F}		1.75		V
Reverse Current	$V_R = 650V$, $T_J = 25$ °C	I_R		1		μΑ
Reverse Current	V _R = 650V, T _J = 175°C	I _R		20		μΑ
ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	$V_R = 400V, T_J = 25^{\circ}C$					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Q_{C}		29		nC
						_
Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C	С		457		pF
Total Capacitance Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C $V_R = 300V$, $f = 1MHz$, $T_J = 25$ °C	C		457 49.7		pF pF
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THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.671		K/W



REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics I_F vs. V_F

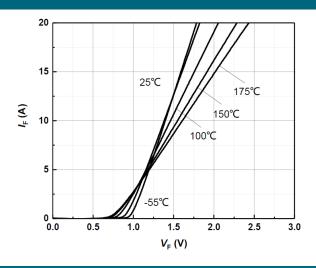


Fig. 2 • Typical Reverse Current I_R as function of Reverse Voltage V_R

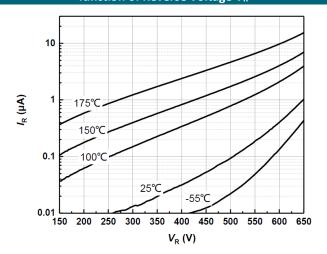


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_C (D = Duty Cycle)

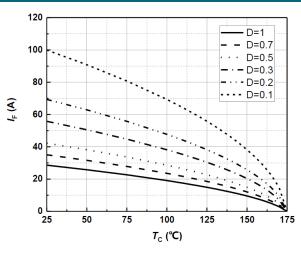


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V_R , $C = f(V_R)$, $T_J = 25^{\circ}C$, f = 1MHz

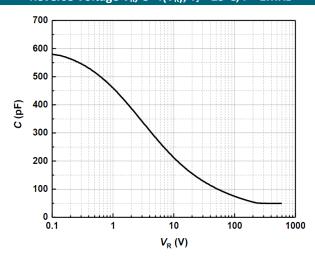


Fig. 5 • Typical Reverse Charge Q_C as function of Reverse Voltage V_R

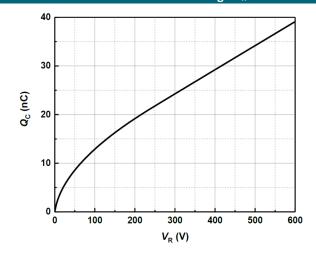
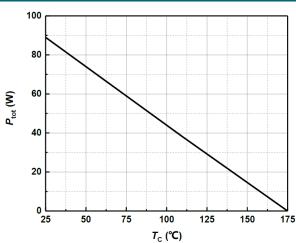


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_c



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REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

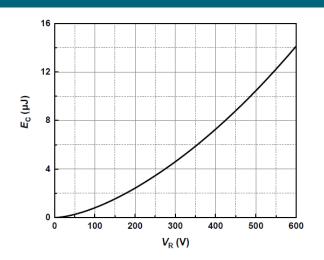
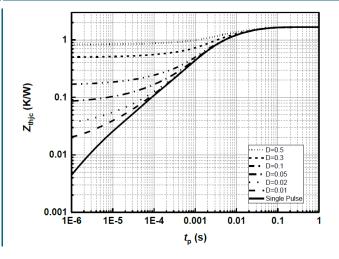
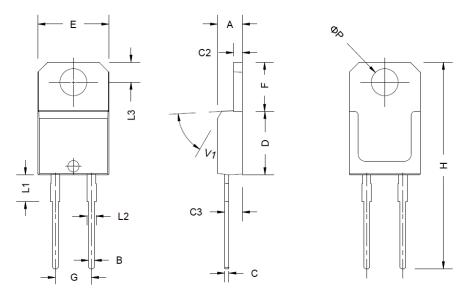


Fig. 8 • Maximum Transient Thermal Impedance, Z_{thjc} = f(t), Parameter: D = t/T





PACKAGE OUTLINE





Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.40	4.50	4.60
В	0.61	0.75	0.88
С	0.46	0.58	0.70
C2	1.21	1.265	1.32
C3	2.40	2.56	2.72
D	8.60	9.15	9.70
Е	9.80	10.10	10.40
F	6.55	6.75	6.95

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
G		5.08 BSC	
Н	28.00	28.90	29.80
L1	-	3.75	-
L2	1.14	-	1.70
L3	2.65	2.80	2.95
V1	-	45°	-
ØР	-	-	3.88

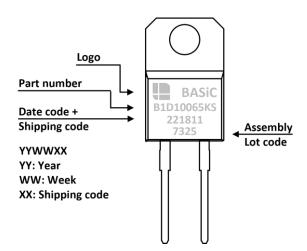
TO-220 ISO-2L package ▲ Epoxy meets UL94-V0

ORDERING INFORMATION

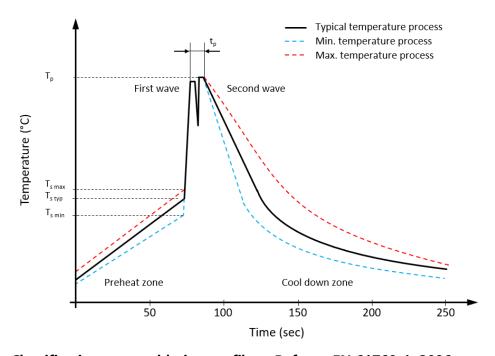
Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D10065KS	TO-220 ISO-2L	Tube	50pcs	500pcs	5,000pcs



PART MARKING



RECOMMENDED WAVE SOLDERING PROFILE & THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	T_{smin}	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	$T_{s max}$	130 °C	130 °C
Preheat time t_s from T_{smin} to T_{smax}	ts	70 seconds	70 seconds
Peak temperature	T_p	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes

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REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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